Physics and Technology of High-k Gate Dielectrics III

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Table of Contents

Preface iii

Chapter 1
High Mobility Substrates

Electrical and Structural Properties of High-K HfO_2 on Si_{1-X} Ge_x Substrates 3
C. Hwang, T. Park, J. Kim, S. H. Hong, M. Seo, and J. H. Jang

Characterization of Atomic-Beam Deposited $GeO_{1-x}N_x/HfO_2$ Stacks on Ge 9
M. Houssa, T. Conard, J. Van Steenbergen, G. Mavrou, Y. Panayiotatos, T. Dimoulas, M. Meuris, M. Caymax, M. Heyns, and G. Nicholas

Effect of Nitridation on Ge/HfO_2 Interface 17
R. Garg, D. Misra, and S. Guha

Interface Trap Characterization and Fermi Level Pinning in Si-Passivated Ge/HfO_2 Capacitors 27
K. Martens, B. Kaczer, P. Roussel, G. Groeseneken, and H. Maes

Characteristics of Thermally Oxidized-Ti as a High-k Gate Dielectric on SiC Metal-Oxide-Semiconductor Devices 33
R. Mahapatra, N. Poolamai, N. Wright, A. K. Chakraborty, K. S. Coleman, K. Das, S. K. Ray, P. Coleman, and P. Burrows

*Advanced High K Dielectrics for Nano Electronics - Science and Technologies 41
M. Hong and J. Kwo

Chapter 2
High-k Materials for Non-Volatile Memory

*High-K Materials for Nonvolatile Memories 63
M. Specht, M. Staedele, F. Hofmann, H. Reisinger, M. Grieb, and L. Risch

*High-k Materials for Tunnel Barrier Engineering in Floating-Gate Flash Memories 75
P. Blomme, B. Govoreanu, M. Rosmeulen, A. Akheyar, L. Haspeslagh, J. De Vos, M. Lorenzini, J. Van Houdt, and K. De Meyer

*High-k Materials in Flash Memories 91
M. Alessandri, R. Piagge, S. Alberici, E. Bellandi, M. Caniatti, G. Ghidini, A. Modelli, G. Pavia, E. Ravizza, A. Sebastiani, C. Wiemer, S. Spiga, M. Fanciulli, V. Fiorentini, E. Cadelano, and G. Lopez

Characterization of Charge Storage in ALD Nanolaminates 107
T. E. Seidel, A. Srivastava, Z. Zhang, T. Dimitrova, A. R. Londergan, and Z. Karim

Investigation of Current Conduction Mechanism in HfO_2 Stack Structures 117
Y. Chiou, S. Gaddipati, M. Mansouri, S. Jeedigunta, and A. Kumar

Chapter 3
High-k Materials for DRAM

*Recent Developments in ALD Technology for 50 nm Trench DRAM Applications 125
U. Schroeder, S. Jakschik, E. Erben, A. Avellan, S. P. Kudelka, M. Kerber, A. Link, and A. Kersch

A Novel Iridium Precursor for MOCVD 133
K. Kawano, T. Furukawa, M. Takamori, K. Tada, T. Yamakawa, N. Oshima, H. Fujisawa, and M. Shimizu

Ruthenium and Ruthenium Oxide Films Deposition by MOCVD Using $Ru(DMPD)_2$ 139
K. Kawano, H. Kosuge, N. Oshima, and H. Funakubo

Compatibility of High K Dielectric with $TiCl_4$ Based TiN for MIS Storage Capacitors for sub 70 nm DT DRAM Technology and Beyond 145
X. Gay, B. Hintze, E. Erben, H. Bernhardt, S. P. Kudelka, C. Goupil, and B. Mercey

Dielectric Properties of $(Zr_xTi_{1-x})O_2$ Film on $Ru/SiO_2/Si$ Substrates Deposited by the Atomic Layer Deposition Using $[Zr(OtBu)_4 + Ti(OtBu)_4]$ Cocktail Source 153
J. Lim, K. Cho, K. Kim, C. Yoo, S. Kim, U. Chung, and J. Moon

Chapter 4
High-k Materials and Processing I

*Rare-Earth Metal Scandate High-k Layers 161
C. Zhao, T. Heeg, M. Wagner, J. Schubert , T. Witters, B. Brijs, H. Bender, O. Richard, V. Afanas'ev, M. Houssa, M. Caymax, and S. De Gendt

Bulk and Interface Material and Electrical Properties of Hafnium-Doped Tantalum Oxide High-K Films 177
Y. Kuo and J. Lu

*Doped HfO_2 for Higher-k Dielectrics 185
A. Toriumi, K. Kita, K. Tomida, and Y. Yamamoto

Chapter 5
High-k Materials and Processing II

A Chemists View of Precursors and Processes for the Production of Hf-Based High K Dielectrics 201
R. D. Clark, A. Hochberg, M. Jahl, K. Cuthill and T. Kok

Crystallization and Wet Etching Characteristics of Atomic Layer Deposited HfO_2 Films Using $Hf([N(CH_3)(C_2H_5)]_3[OC(CH_3)_3])$ Precursor and O_3 Oxidant 211
M. Seo, S. Kim, K. Kim, T. Park, J. Kim, C. Hwang, and H. Cho

Annealing Effect and Suppression of Hydration of La_2O_3 Thin Films 219
D. Eom, S. No, C. Hwang, and H. Kim

High-Temperature Processing Effects on Lanthanum Silicate Gate Dielectric MIS Devices 227
D. J. Lichtenwalner, J. Jur, N. Inoue, and A. Kingon

Al/La_2O_3 Analysis of Post Metallization Annealed MISFET by XPS 239
Y. Kuroki, J. Ng, K. Kakushima, N. Sugii, K. Tsutsui, and H. Iwai

Y-Doped HfO_2 Thin Films Grown by Injection MOCVD 249
E. Rauwel Buzin, F. Ducroquet, M. Rossell, J. Verbeeck, G. Van Tendeloo, B. Hollaender, S. Rushworth, and C. Dubourdieu

Influence of an In-Situ Formed Interfacial SiN_x Layer on the Electrical Performance and Thermal Stability of High-k HfO_2 Films 257
S. H. Hong, J. Kim, T. Park, J. Won, R. Jung, S. Kim, C. Hwang, and M. J. Cho

Chapter 6
Gate Electrode Materials I

*Prospect of Hf-Based Gate Dielectric by PVD with FUSI Gate for LSTP Application 269
M. Niwa, R. Mitsuhashi, S. Hayashi, K. Yamamoto, Y. Harada, M. Kubota, A. Rothchild, T. Hoffmann, S. Kubicek, S. De Gendt, M. Heyns, A. Lauwers, S. Biesemans, and J. Kittle

Thermal Robustness of VFB and EOT in HfO_x(N) p-MOS Devices with Partially Silicided Pt Gate Electrodes 287
M. Kadoshima, T. Nabatame, M. Takahashi, A. Ogawa, K. Iwamoto, W. Mizubayashi, H. Ota, H. Satake, and A. Toriumi

Workfunction Tuning of Nickel Silicide by Varying Nickel and Silicon Composition 295
N. Biswas, S. Novak, B. Lee, B. Chen, and V. Misra

Threshold Voltage Control in PMOSFETs with Polysilicon or Fully-Silicided Gates on Hf-Based Gate Dielectric Using Controlled Lateral Oxidation 305
V. S. Kaushik, E. Rohr, S. Hyun, S. De Gendt, S. Van Elshocht, A. Delabie, J. Everaert, A. Veloso, S. Brus, L. Ragnarsson, O. Richard, M. Caymax, and M. Heyns

Chapter 7
Physical/Chemical Characterization

*The Influence of NH_3 Anneal on the Crystallization Kinetics of HfO_2 Gate Dielectric Films 313
P. Lysaght, J. Barnett, J. Woicik, B. Foran, G. Bersuker, and B. Lee

Advanced Nano-analysis of High-k Dielectric Stacks 323
M. MacKenzie, A. Craven, D. McComb, and S. De Gendt

Structural Effects in the Dielectric Constant of Rare-Earth Oxides: Nd_2O_3 331
T. Busani, R. Devine, and P. Gonon

Microscopic and Spectroscopic Analysis of High-k Oxide HfO_x Films 341
J. Park, R. Jung, and Y. Cho

*Probing Point Defects in Stacks of Ultrathin High-k Metal Oxides on Semiconductors by Electron Spin Resonance: The Si/HfO_2 vs. the Ge/HfO_2 System 347
A. Stesmans, V. Afanas'ev, and K. Clemer

Chapter 8
Interfaces and Defects

*Materials Interaction at the Nanoscale in High-k Metal Gate Stacks: The Role of Oxygen 363
S. Guha, E. Preisler, N. Bojarczuk, and M. Copel

Effect of a Se Monolayer on Interface Properties Between Al_2O_3 and n-type Si(100) 371
G. Larrieu, M. Tao, N. Moumem, G. Song, E. Moldonado, and W. Kirk

Band Edge Traps at Spectroscopically-Detected O-Atom Vacancies in Nanocrystalline ZrO_2 and HfO_2: An Engineering Solution for Elimination of O-Atom Vacancy Defects in Non-crystalline Ternary Silicate Alloys 381
G. Lucovsky, J. Luning, N. A. Stoute, H. Seo, C. L. Hinkle, and B. Ju

Improvement in Thermal Stability of MOCVD HfO_2 Films Using an ALD SiN_x Interfacial Layer 393
H. J. Jang, S. H. Hong, T. Park, J. Heo, S. Yang, M. Kim, and C. Hwang

Effects of the Defects at HfO_xN_y/Si Interface on Electrical and Reliability Characteristics of MOS Devices 399
K. Chang-Liao, C. L. Cheng, C. Y. Lu, C. H. Huang, S. H. Wang, and T. K. Wang

Formation of Pedestal Oxynitride Layer by Extremely Shallow Nitrogen Implantation in Planar R.F. Plasma Reactor 407
T. Bieniek, R. Beck, A. Jakubowski, P. Hoffmann, D. Schmeisser, P. Konarski and M. Cwil

Influence of Deposition Temperature of Atomic-Layer-Deposited HfO_2 Films on Interfacial Chemical Structure and Interface Trap Density 419
J. Kim, T. Park, C. Hwang, S. H. Hong, and M. Seo

A Simple Approach to Reduce Interlayer Formation of Sputtered Hf-Based Gate Dielectrics by Nitrogen Incorporation 425
J. Chen, C. Lu, and Y. Lai

Chapter 9
High-k Materials and Processing III

*Growth Studies and Reaction Mechanism of the Atomic Layer Deposition of Hafnium Oxide 433
A. Delabie, M. Caymax, B. Brijs, D. Brunco, T. Conard, E. Sleeckx, L. Ragnarsson, S. Van Elshocht, S. De Gendt and M. Heyns

Sub 2 nm Thick Zirconium Doped Hafnium Oxide High-K Gate Dielectrics 447
Y. Kuo, J. Lu, J. Yan, T. Yuan, H. Kim, J. Peterson, M. Gardner, S. Chatterjee, and W. Luo

Ultra-Thin HfON Films Formed with He/FG Plasma Jet Assisted PVD Process 455
Y. Liu, S. Wang, T. Ma, L. Lee, M. Tsai, and Y. Chou

Characteristics of the HfO_2 Thin Films Grown by Remote Plasma Atomic Layer Deposition Method on the Plasma Oxidized Si Substrate 459
H. Kang, S. Kim, J. Kim, J. Choi, H. Jeon, and C. Bae

Quality Improvement and Electrical Characteristics of High-k Films after Receiving Direct Superimposed with Alternative Current Anodic Oxidation Compensation 465
J. Hwu, C. Chang, and T. Wang

Chapter 10
Gate Electrode Materials II

*Theoretical Studies on the Physical Properties of Poly-Si and Metal Gates/HfO_2 Related High-k Dielectrics Interfaces 479
K. Shiraishi, K. Torii, Y. Akasaka, T. Nakayama, T. Nakaoka, S. Miyazaki, T. Chikyow, K. Yamada, and Y. Nara

Evaluation of Nb(Si)N as Metal Gate Material 495
N. Van Hoornick, H. De Witte, T. Witters, C. Zhao, T. Conard, H. Huatori, J. Swerts, T. Schram, J. Maes, S. De Gendt, and M. Heyns

Impact of Al, Ni, and TiN Metal Gates On ZrO_2-MOS Capacitors 507
S. M. Abermann, J. Efavi, A. Lugstein, E. Auer, H. Gottlob, M. Schmidt, M. Lemme, and E. Bertagnolli

Post Metallization Anneal Effects in HfO_2 Based Capacitors with Various Gate Electrodes 517
Y. Lu, O. Buiu, I. Mitrovic, S. Hall, P. R. Chalker, R. Potter, A. Nazarov, V. Lysenko, I. Tyagulskii, I. Osiyuk, and Y. Vovk

Dielectric Evolution Characteristics of HfCN Metal Electrode Gated MOS Stacks 529
W. Wang, T. Nabatame, and Y. Shimogaki

Chapter 11
Electrical and Reliability Characterization I

*Composition Dependence of Physical and Electrical Properties of HfSiON Films as Alternative Gate Dielectrics 541
A. Nishiyama, M. Koike, Y. Kamimuta, M. Suzuki, T. Ino, and M. Koyama

Determination of the Channel Doping Density in MOS Devices with High-K Gate Dielectrics 553
S. Kar and D. Reddy

Study of Charge and Inversion Layer Mobility in Hafnium Oxide Stacks 565
Z. Zhang, M. Li, and S. Campbell

A Radar for Ultra-thin High-k Dielectric Film: Zero-Bias Thermally Stimulated Current Spectroscopy 577
W. Lau, T. Han, G. L. Zhang, P. W. Qian, L. L. Leong, S. T. Che, and P. Wong

*Charge Trapping & NBTI in High k Gate Dielectric Stacks 591
S. Zafar, A. Callegari, and J. Stathis

Chapter 12
High-k Transistor Performance

*High Performance Metal Gate CMOSFETs with Aggressively Scaled Hf-Based High-k 609
S. Song, G. L. Zhang, S. Bae, P. Kirsch, P. Majhi, R. Choi, and B. Lee

Influence of Ta(N) Metal Gate Microstructure on Its Etch Properties 625
D. Shamiryan, V. Paraschiv, Z. Tokei, and W. Boullart

Wet Etch Characteristics of Hafnium Silicate Layers 633
M. Claes, V. Paraschiv, D. Dictus, T. Conard, W. Boullart, S. Vanhaelemeersch, S. De Gendt, A. Delabie, S. Van Elshocht, C. Zhao, and J. Everaert

*HfSiON Gate Dielectrics for hp45 Node and Beyond 645
Y. Nara, S. Inumiya, K. Torii, and K. Nakamura

*CMOS Integration Issues with High-K/Metal Gate Stack 653
D. Kwong

Chapter 13
Electrical and Reliability Characterization II

*Charge Trapping Effects in High-k Transistors 663
G. Bersuker, J. Sim, C. Young, R. Choi, C. Park, and B. Lee

Charge Capture Kinetics of Nitride Trap in Oxide-Nitride-Oxide Structures 671
H. Cho, C. Park, H. Oh, D. Kwak, Y. Lee, W. Yang, and C. Kim

Effect of Nitridation on 1/f Noise in n-MOSFETs with High-k Dielectric 681
P. Srinivasan, E. Simoen, C. Rittersma, L. Pantisano, C. L. Claeys, and D. Misra

Efficient Calculation of Lifetime Based Direct Tunneling Through Stacked Dielectrics 693
M. Karner, A. Gehring, S. Holzer, H. Kosina, and S. Selberherr

Implications of Non-Linear Poole-Frenkel Plots on High-k Dielectric Leakage 705
W. R. Harrell, T. Cordella, and K. Poole

*New Insights in Hf Based High-k Gate Deielectrics in MOSFETs 717
M. Li, C. Zhu, C. Shen, X. Yu, Y. Feng, Y. Yeo, A. Chin, D. Kwong, S. H. Wang, A. Du, and G. Samudra

Chapter 14
Electrical and Reliability Characterization III

*Charge Trapping: A Major Reliability Challenge for High-k Gate Dielectrics 733
T. Ma, S. Wang, L. Song, and H. Bu

Salient Features in the Capacitance Characteristics of Ultrathin High-K Devices 745
S. Kar, D. Reddy, and S. Rawat

Electrical Breakdown and Reliability of Metal Gate - La_2O_3 Thin Films after Post Deposition Annealing in N_2 757
J. Molina, K. Tsutsui, H. Iwai, K. Kakushima, N. Sugii, and P. Ahmet

Evidence of Deep Energy States from Low Temperature Measurements and Its Role in Charge Trapping in Metal Gate/Hf-Silicate Gate Stacks 767
N. A. Chowdhury, P. Srinivasan, and D. Misra

Asymmetric Distribution of Charge Trap in HfO_2-Based High-k Gate Dielectrics 777
K. Higuchi, T. Naito, A. Uedono, K. Shiraishi, K. Torii, M. Boero, T. Chikyow, S. Yamasaki, K. Yamada, R. Hasumuma, and K. Yamabe

Indication of Lateral Nonuniformity of Effective Oxide Charges in High-k Gate Dielectrics by Terman's Method 789
J. Hwu and S. Huang

Author Index

** Invited Papers*